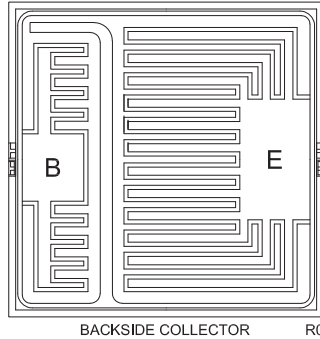


**CP527-2N6299**  
**PNP - Darlington Transistor Die**  
**8.0 Amp, 80 Volt**

The CP527-2N6299 is a silicon PNP Darlington power transistor designed for high gain amplifier applications.



**MECHANICAL SPECIFICATIONS:**

Die Size	110 x 110 MILS
Die Thickness	10.6 MILS
Base Bonding Pad Size	21 x 24 MILS
Emitter Bonding Pad Size	24 x 42 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Ni/Ag - 2,000Å/10,000Å
Scribe Alley Width	4.3 mils
Wafer Diameter	4 INCHES
Gross Die Per Wafer	875

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

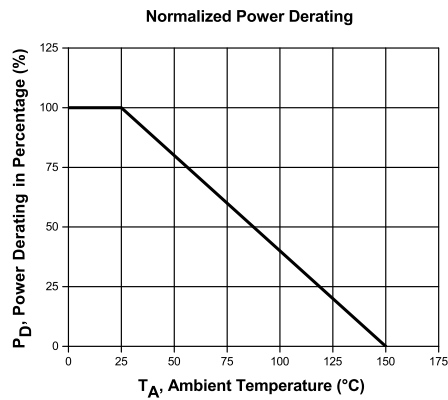
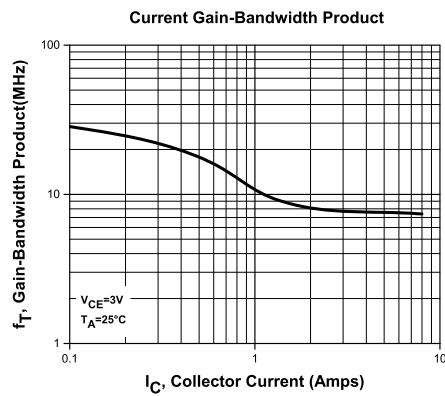
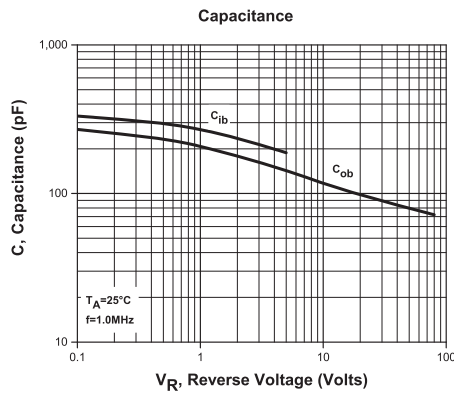
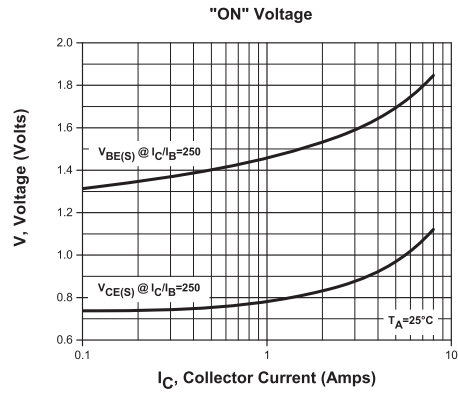
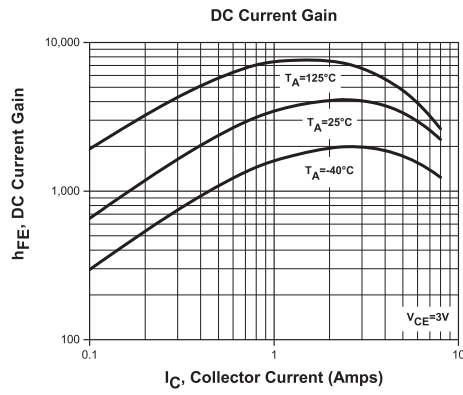
	SYMBOL		UNITS
Collector-Base Voltage	$V_{CB0}$	80	V
Collector-Emitter Voltage	$V_{CE0}$	80	V
Emitter-Base Voltage	$V_{EB0}$	5.0	V
Continuous Collector Current	$I_C$	8.0	A
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CEV}$	$V_{CE}=80\text{V}, V_{BE}=1.5\text{V}$		0.5	mA
$I_{CEO}$	$V_{CE}=40\text{V}$		0.5	mA
$I_{EBO}$	$V_{EB}=5.0\text{V}$		2.0	mA
$BV_{CEO}$	$I_C=100\text{mA}$	80		V
$V_{CE(SAT)}$	$I_C=4.0\text{A}, I_B=16\text{mA}$		2.0	V
$V_{CE(SAT)}$	$I_C=8.0\text{A}, I_B=80\text{mA}$		3.0	V
$V_{BE(SAT)}$	$I_C=8.0\text{A}, I_B=80\text{mA}$		4.0	V
$V_{BE(ON)}$	$V_{CE}=3.0\text{V}, I_C=4.0\text{A}$		2.8	V
$h_{FE}$	$V_{CE}=3.0\text{V}, I_C=4.0\text{A}$	750	18K	
$h_{FE}$	$V_{CE}=3.0\text{V}, I_C=8.0\text{A}$	100		
$h_{fe}$	$V_{CE}=3.0\text{V}, I_C=3.0\text{A}, f=1.0\text{kHz}$	300		
$f_T$	$V_{CE}=3.0\text{V}, I_C=3.0\text{A}, f=1.0\text{MHz}$	4.0		MHz
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$		300	pF

# CP527-2N6299

## Typical Electrical Characteristics



## OUTSTANDING SUPPORT AND SUPERIOR SERVICES



---

### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

---

### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

---

### REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

---

### CONTACT US

#### Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.  
145 Adams Avenue  
Hauppauge, NY 11788 USA  
Main Tel: (631) 435-1110  
Main Fax: (631) 435-1824  
Support Team Fax: (631) 435-3388  
[www.centrasemi.com](http://www.centrasemi.com)

**Worldwide Field Representatives:**  
[www.centrasemi.com/wwreps](http://www.centrasemi.com/wwreps)

**Worldwide Distributors:**  
[www.centrasemi.com/wwdistributors](http://www.centrasemi.com/wwdistributors)

---

For the latest version of Central Semiconductor's **LIMITATIONS AND DAMAGES DISCLAIMER**, which is part of Central's Standard Terms and Conditions of sale, visit: [www.centrasemi.com/terms](http://www.centrasemi.com/terms)